

**AMENDMENT TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Original) A method for forming a conductive wire of a semiconductor device, comprising:

etching a lower portion of a side wall of a silicon layer pattern based on a difference of etching selectivities between a silicon layer and a lower film; and

forming a T-shaped conductive wire based on the silicon layer pattern.

2. (Original) The method of claim 1, wherein the lower layer comprises an insulating material, wherein the etching selectivity of the insulating material to that of the silicon layer is 1:5 to 500.

3-14 (Cancelled).

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